

Action states it is unclear how the structure of the light-receiving device will be formed when the third semiconductor layer is formed on the surface of the first semiconductor layer and surrounds a plurality of second semiconductor layers that are formed in the first semiconductor layer. In response to this inquiry, the following is submitted.

With reference to Figure 2E, the present invention is directed to a semiconductor light-receiving device including a first conductivity type (n+) semiconductor substrate (1) having a first surface on a light-receiving side and a second surface on the opposite side to the first surface, and a first semiconductor layer (2) formed on the first surface of the semiconductor substrate. Further, a plurality of first conductivity type (n+) second semiconductor layers (4) reach the semiconductor substrate (1) from a surface of the first semiconductor layer (2) and in which the second semiconductor layers (4) are formed apart from each other.

Further, a second conductive type (p+) third semiconductor layer (3) is selectively formed on the surface of the first semiconductor layer (2) and in which the third semiconductor layer (3) surrounds each of the second semiconductor layers (4) with the first semiconductor layer (2) therebetween. This feature is clearly shown in Figures 2D and 2E, for example, in which the third semiconductor layer (3) surrounds each of the second semiconductor layers (4) with the first semiconductor layer (2) therebetween.

In addition, the third semiconductor layer (3) is lying directly under the p-side electrode (5) and in a region corresponding to the region where the p-side electrode (5) exists as shown in Figures 1A and 1B. The third semiconductor layer (3) is hiding under the p-side electrode (5) and does not appear in Figure 1A. The p-side electrode (5) is surrounding the second semiconductor layers (4) in Figure 1A, and the third semiconductor layer (3) is also

surrounding the second semiconductor layers (4) with the first semiconductor layer (2) disposed therebetween with reference to Figure 1B.

Therefore, in light of the above discussion, it is respectfully requested the rejection of Claims 1-22 under 35 U.S.C. §112, second paragraph be withdrawn.

Consequently, in light of the above discussion, the present application is believed to be in condition for allowance and an early and favorable action to that effect is respectfully requested.

Respectfully submitted,

OBLON, SPIVAK, McCLELLAND,
MAIER & NEUSTADT, P.C.



Gregory J. Maier
Attorney of Record
Registration No. 25,599
David A. Bilodeau
Registration No. 42,325



22850

(703) 413-3000
Fax #: (703)413-2220
DAB/rac
I:\atty\DAB\204404US-AM.wpd